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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Atty. Docket No.

26068-27B

Charles Ahn et al.

Serial No.:

10/582,813

Art Unit:

2818

Filed:

June 14, 2006

Title:

Magnetoelectronic Devices Based on Colossal Magnetoresistive Thin

Films

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Pursuant to Sections 609 and 707.05(b) of the MPEP and 37 CFR 1.97-1.99, the attached form PTO-1449 lists documents that may be pertinent to the invention as claimed in the above-identified application.

This Information Disclosure Statement is being filed before the mailing date of a first Office action on the merits and therefore, no fee is believed to be due. In the event that a fee is due, please charge Deposit Account No. 50-0447 to cover these fees. The citation of these documents should not be construed as a representation that a thorough search has been made, or that other, more pertinent material is not available.

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Respectfully submitted,

By: \(\tag{ \ta} \tag{ \} \} \tag{ \tag{ \tag \} \} \tag{ \tag} \} \tag{ \tag{ \tag{ \ta}

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INFORMATION DISCLOSURE PATENT APPLICATION

(FORM PTO-1449)

Docket No.: 26068-27B

Serial No.: 10/582,813

Applicant: Charles Ahn et al.

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